

REMARKS

Claims 8, 9 and 11-13 are pending in this application. By this Amendment, claim 8 has been amended. Support for the amendment to claim 8 can be found at least at pg. 7, lines 1-22 of the specification and at least in Figs. 1-11. Thus, no new matter has been added.

I. 35 U.S.C. §103 Rejections

The Office Action rejects claims 8-12 under 35 U.S.C. §103(as) as being obvious over U.S. Patent Application Publication No. 2002/0047172 to Reid (hereinafter "Reid") in view U.S. Patent No. 5,835,256 to Huibers (hereinafter "Huibers") and WO 00/33089 to Mathieu et al. (hereinafter "Mathieu"), and further in view of U.S. Patent No. 5,985,748 to Watts (hereinafter "Watts") and U.S. Patent No. 6,090,712 to Lyons (hereinafter "Lyons"), and rejects claim 13 under 35 U.S.C. §103(a) as being unpatentable over Reid in view of Huibers and Mathieu, and further in view of U.S. Patent Application Publication No. 2003/0183887 to Lee et al. (hereinafter "Lee").

Applicants note that claim 10 was canceled by the Amendment filed on June 13, 2008. Accordingly, the rejection of claim 10 is moot. The rejection with respect to pending claims 8, 9 and 11-13 is respectfully traversed.

Claim 8 has been amended to recite, in part, "deposition, on at least part of the substrate and on at least part of the front face of the sacrificial layer, of the embedding layer presenting a larger thickness than the thickness of the sacrificial layer, the embedding layer surrounding the sacrificial layer, an interface being formed between the sidewalls of the sacrificial layer and internal sidewalls of the embedding layer, planarization of the embedding layer such that the front face of the sacrificial layer and a front face of the embedding layer form a common flat surface, the embedding layer still surrounding the sacrificial layer" (emphasis added). None of the applied references, taken alone or in combination, disclose or

render obvious, the above-quoted features of claim 8, and the similar features recited by claim 13.

As shown in Fig. 2B, Reid discloses depositing a sacrificial layer 42 of amorphous silicon by a PECVD or PVD process on a circuit substrate 40. Reid discloses that the sacrificial layer 42 may then be patterned to form an aperture. A plug layer 43, which is a metal compound, is then deposited over the sacrificial layer 42 so as to fill the aperture. The plug layer 43 and the sacrificial layer 42 are then planarized (see Fig. 2C). However, after planarization, the sacrificial layer 42 surrounds the plug 44. Thus, Reid fails to disclose "planarization of the embedding layer such that the front face of the sacrificial layer and a front face of the embedding layer form a common flat surface, the embedding layer still surrounding the sacrificial layer," (emphasis added) as recited by claim 8, and as similarly recited by claim 13.

Further, Huibers fails to disclose an embedding layer that surrounds a sacrificial layer. As shown in Figs. 1, 2, 3, and 7A-7C of Huibers, the attachment regions 54 do not surround the sacrificial material even if several micro-devices are manufactured on a single substrate. Thus, Reid, taken alone or in combination with Huibers, fails to disclose "the embedding layer surrounding the sacrificial layer, an interface being formed between the sidewalls of the sacrificial material and internal sidewalls of the embedding layer, planarization of the embedding layer such that the front face of the sacrificial layer and a front face of the embedding layer form a common flat surface, the embedding layer still surrounding the sacrificial layer," (emphasis added) as recited by claim 8, and as similarly recited by claim 13.

Further, none of the other applied references cure at least the above-stated deficiencies of Reid and Huibers.

Therefore, claims 8 and 13 are patentable over the applied combination of references. Claims 9, 11 and 12 are also patentable for at least their various dependencies from claim 8 as well as for the additional features they recite.

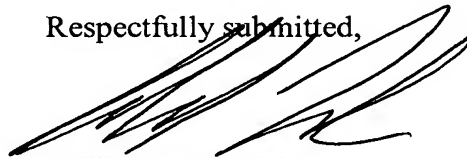
Accordingly, withdrawal of the rejections is respectfully requested.

II. Conclusion

In view of the foregoing, it is respectfully submitted that this application is in condition for allowance. Favorable reconsideration and prompt allowance are earnestly solicited.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number set forth below.

Respectfully submitted,



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